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HIGH VOLTAGE MOS DEVICES WITH HIGH GATED-DIODE
BREAKDOWN VOLTAGE AND PUNCH-THROUGH VOLTAGE

ABSTRACT OF THE DISCLOSURE

5 A method of fabricating CMOS devices suitable for
high voltage and low voltage applications, while maintaining
minimum channel lengths for the devices. In one embodiment,
pocket implants (310) are formed in a minimum channel device
causing a reverse channel effect. The reverse channel effect
is optimized for the minimum channel length of the device.
10 Field implants (120), enhancement implants (130), and wells
(140) are all formed using a single mask.

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